

FEATURES

Low power consumption.

High Efficiency

Round type

T1 (5mm) diameter

With Flange

Solder leads without stand-off

Compliant with RoHS

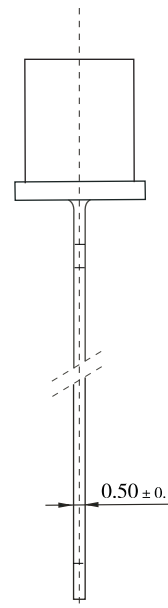
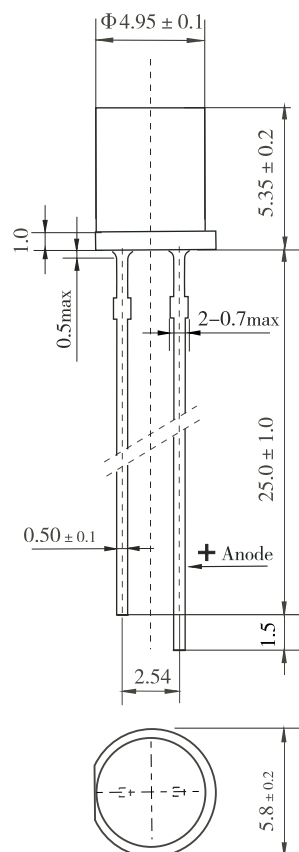
DESCRIPTIONS

Chip Material: InGaN/CaN

Emitting Color: Blue

Lens Color: Water Clear

OUTLINE DRAWING



ATTENTION



OBSERVE PRECAUTIONS
FOR HANDLING
ELECTROSTATIC
SENSITIVE DEVICES

Tolerance is $\pm 0.25\text{mm}$

Unless Otherwise Specified.

ELECTRICAL OPTICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Forward Voltage	V_F	—	3.1	3.4	V	IF=20mA
Luminous Intensity	I_v	150	220	—	mcd	IF=20mA
Peak Wavelength	λ_p		455		nm	IF=20mA
Spectral Line half-width	$\Delta \lambda$		20		nm	IF=20mA
Reverse Leakage Current	I_R			50	μA	VR=5V
Viewing Angle	$2\theta_{1/2}$		100		Deg	IF=20mA

ABSOLUTE MAXIMUM PARAMETERS (Ta=25°C)

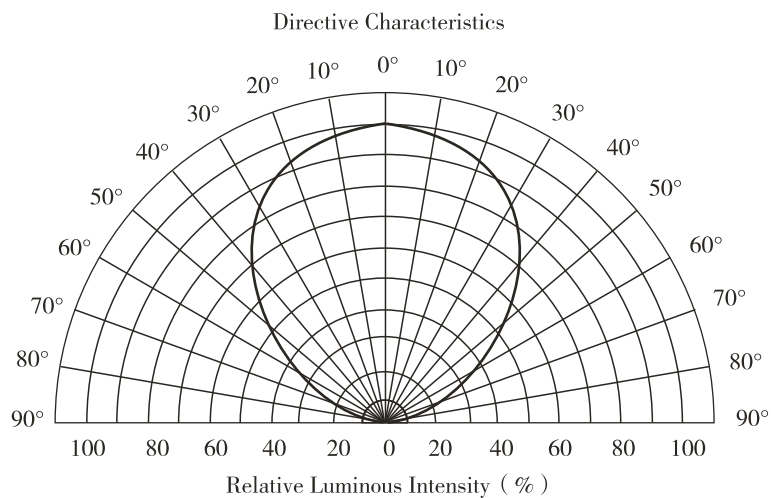
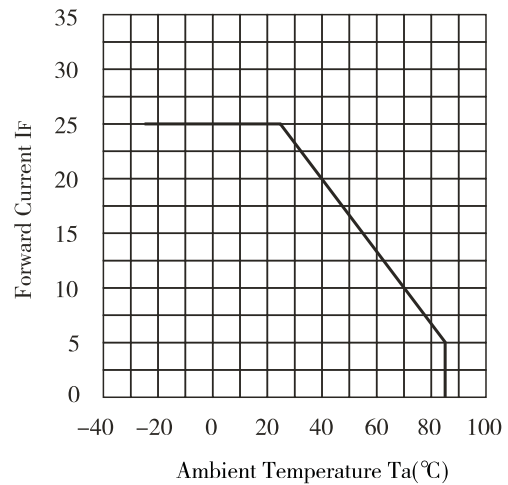
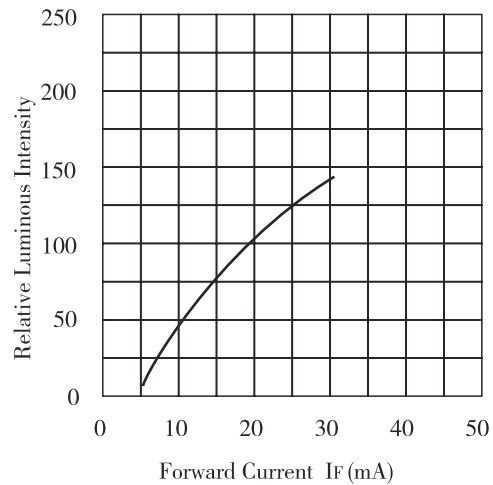
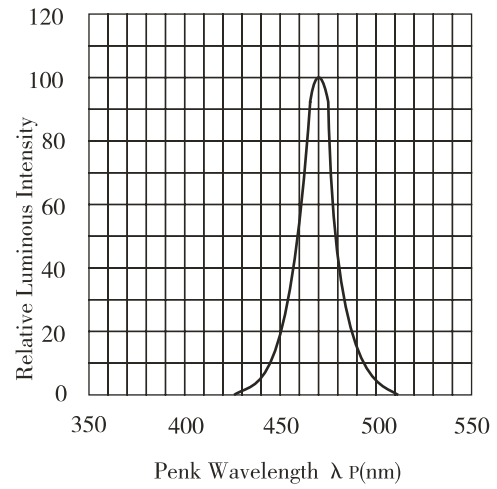
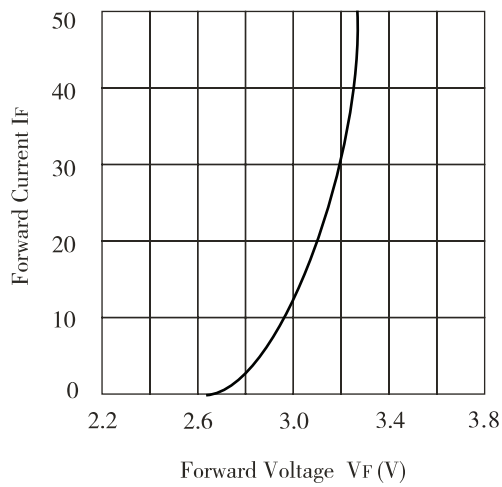
Parameter	Symbol	Condition	Rating	Unit
Power Dissipation	P_D	---	100	mW
Reverse Voltage	V_R	IR=50 μA	5	V
Forward Average Current	I_F	---	30	mA
Temperature coefficient	I/C	---	0.4	mA/ °C
Pulse Current	IFP	Duty=1/10,1kHz	100	mA
Operating Temperature Range	Topr	---	-25 ~ +85	°C
Storage Temperature Range	Tstg	---	-30 ~ +100	°C
Soldering Condition	Tsd	---	265°C/5sec	°C

NOTE:

Luminous Intensity Measurement allowance is $\pm 10\%$.

$2\theta_{1/2}$ is the off-axis angle at which the luminous intensity is half the axial luminous intensity.

The dominant wavelength is derived from the CIE chromaticity diagram and represents the single wavelength which defines the color of the device.

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES ($T_a=25^{\circ}\text{C}$)


Luminous Intensity Ranks(IF=20mA Ta=25°C)

Bin Code	Min(mcd)	Max(mcd)
M	145	200
N	200	280
P	280	390
Q	390	550